

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Yi Ding

Assignee:

Mosel Vitelic, Inc.

Title:

Nonvolatile Memory Cell With Multiple

Floating Gates Formed After the Select Gate

Application No.:

10/631,941

Filing Date:

July 30, 2003

Examiner:

Unknown

Group Art Unit:

Unassigned

Docket No.:

M-15171 US

San Jose, California September 17, 2003

Director of USPTO P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

- an admission that the documents are necessarily prior art with respect to the instant invention:
 - 2. a representation that a search has been made, other than as described above; or
- 3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Director of USPTO, P.O. Box 1450, Alexandria, VA 22313-1450, on September 17, 2003.

Attorney for Applicant

Respectfully submitted,

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Michael Shenker

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SEP 2 2 2003

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Michael Stienker

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| U.S. Department of Commerce, Patent and Trademark Office | | | | | Atty Docket No. | | Serial No. | |
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| | AR | Nonvolatile Memo | ories From Layers S. | | ortions," Filed o | on May 16, | 2003; Attorney Docket | |
| | AS | United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US. United States Patent Application No. 10/440,508, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories Having Select, Floating And Control Gates," Filed on May 16, 2003; Attorney Docket No.: M-15204 US. | | | | | | |
| | AT | | | | | | | |
| | AU | United States Patent Application No. 10/440,500, entitled "Integrated Circuits With Openings that Allow Electrical Contact To Conductive Features Having Self-Aligned Edges," Filed on May 16, 2003; Attorney Docket No.: M-15205 US. | | | | | | |
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| *EXAMINER | R: Initial in confo | if reference consider rmance and not cons | red, whether or no idered. Include co | ot citation is in conf opy of this form wi | formance with M th your commun | IPEP 609; nication to | Draw line through applicant. | |

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| B. | OTHE | ER ART (Including Author, Title, | , Date, Pertinent Pages, Etc.) | | | | | |
| SEP 1 | United State Fabrication, | es Patent Application No. 10/393,2" Filed on March 19, 2003; Attorne | | ries And Methods Of | | | | |
| A | | United States Patent Application No. 10/411,813, entitled "Nonvolatile Memories With A Floating Gate Having An Upward Protrusion," Filed on April 10, 2003; Attorney Docket No.: M-12903 US. | | | | | | |
| A | United State Structures V | United States Patent Application No. 10/393,202, entitled "Fabrication of Integrated Circuit Eleme Structures With Protruding Features," Filed on March 19, 2003; Attorney Docket No.: M-15151 U | | | | | | |
| A | AY United States Patent Application No. 10/632,155, entitled "Nonvolatile Memory Cells With Buried Channel Transistors," Filed on July 30, 2003; Attorney Docket No.: M-15222 US. | | | | | | | |
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| I | | United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US. | | | | | | |
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